## APD Semiconductor, Inc.

SBR20150CT-prel SBR20150CTI-prel SBR20150CTB-prel

# Super Barrier Rectifier TM

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

### Major ratings and characteristics

Characteristics	Values	Units	
$I_{F(AV)}$ Rectangular Waveform	20	А	
V <sub>RRM</sub>	150	V	
I <sub>R</sub> @150V, Tj=25°C	12	nA, typ	
Tj(operating/storage)	-65 to 200	°C	

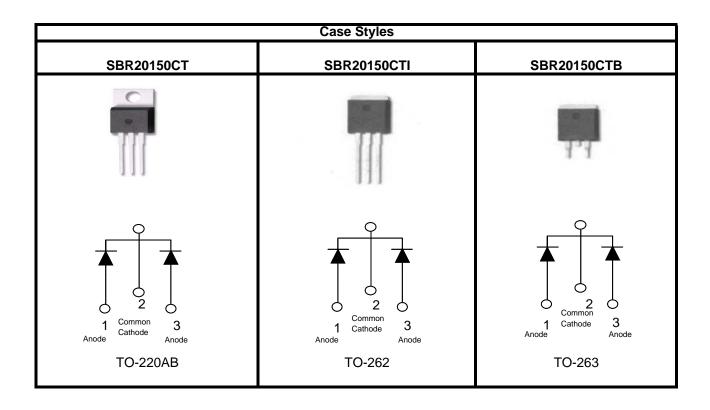
### ELECTRICAL:

- \* Ultra High Thermal Reliability
- \* Low Reverse Leakage
- \* Reliable High Temperature Operation
- \* Super Barrier Design
- \* Softest, fast switching capability
- \* 200°C Operating Junction Temperature

### Device optimized for high temperature Power Supply applications

MECHANICAL:

\* Molded Plastic TO-220AB, TO-262, TO-263 packages



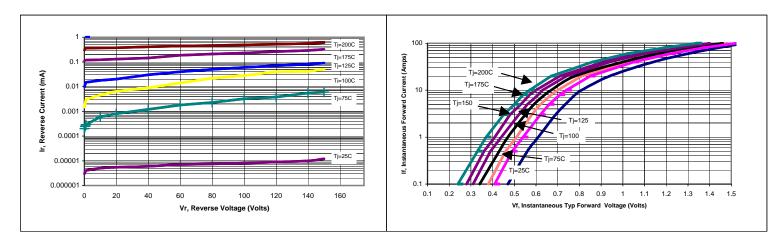


	SYMBOL			UNITS
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	V <sub>RM</sub> V <sub>RWM</sub> V <sub>RRM</sub>	150		Volts
RMS Reverse Voltage	V <sub>R(RMS)</sub>	150		Volts
Average Rectified Forward Current (Rated V <sub>R</sub> -20Khz Square Wave)-50% duty cycle	I <sub>o</sub>	20		Amps
Peak Forward Surge Current - 1/2 60hz	I <sub>FSM</sub>	180		Amps
Peak Repetitive Reverse Surge Current (2uS-2Khz)	I <sub>RRM</sub>	3		Amps
Instantaneous Forward Voltage (per leg) $I_F = 10A; T_J = 25^{\circ}C$ $I_F = 20A; T_J = 25^{\circ}C$ $I_F = 10A; T_J = 125^{\circ}C$	V <sub>F</sub>	Typ 0.82 0.94 0.67	Max 0.86 0.98 0.71	Volts
Maximum Instantaneous Reverse Current at Rated $V_{RM}$ T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C	I <sub>R</sub> *	Тур 0.012 0.09	Max 5 1	uA mA
Maximum Rate of Voltage Change (at Rated $V_{R}$ )	dv/dt	10,000		V/uS
Maximum Thermal Resistance JC	$R\theta_{JC}$	2		°C/W
Operating and Storage Junction Temperature	TJ	-65 to +200		°C

NOTE: Dice are available for customer applications.

\* Pulse width < 300 uS, Duty cycle < 2%

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**Figure 1: Typical Reverse Current** 

**Figure 2: Typical Forward Voltage** 

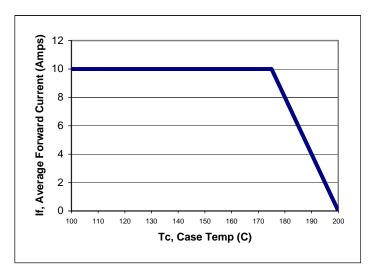


Figure 3: Current Derating, Case

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